

by two-step deposition of [selective tungsten] metal layers, said method comprising the steps of:

providing a silicon substrate;

forming a field oxide layer and a junction layer and gate electrode on said silicon substrate;

forming a first insulating layer on [the whole structure] exposed portions of the field oxide layer, the junction layer, and the gate electrode;

forming first plurality of contact holes of substantially equal depth by removing [desired] portions of the first insulating layer to expose said junction layer and said gate electrode, respectively;

filling a first metal [layers] layer into the first plurality of contact holes, entirely;

forming a conductive layer pattern on the first insulating layer spaced from said first metal [layers] layer;

forming a second insulating layer on [the whole structure] exposed portions of the conductive layer pattern, the first insulating layer, and the first plurality of contact holes;

forming [a plurality of] second plurality of contact holes of substantially equal depth by removing [desired] portions of said second insulating layer to expose both the first metal [layers] layer and the conductive layer pattern, respectively; and

filling a second metal [layers] layer into said second plurality of [second] contact holes to contact [with] the first metal [layers] layer and the conductive layer pattern, respectively.

2. (Amended) [The methods of] A method according to claim 1, wherein the first metal layer and subsequently the second metal layer are formed by chemical vapor deposition method.